

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A pn junction type Group III nitride semiconductor light-emitting device comprising a light-emitting layer of multiple quantum well structure in which well layers and barrier layers including Group III nitride semiconductors are alternately stacked periodically between an n-type clad layer and a p-type clad layer which are formed on a crystal substrate and which include Group III nitride semiconductors,

wherein a first end layer of the light-emitting layer is closest to and opposed to the n-type clad layer, and a second end layer of the light-emitting layer is closest to and opposed to the p-type clad layer, both the first and second end layers are barrier layers, and the second end layer is thicker than the barrier layer of the first end layer, and

wherein the barrier layers other than the second end layer have a thickness of 15 nm or more and 50 nm or less, and the second end layer has a thickness of 1.2 or more times and 2.5 or less times the thickness of the barrier layers other than the second end layer.

2. (previously presented): The pn junction type Group III nitride semiconductor light-emitting device according to claim 1, wherein each of the barrier layers has a thickness increased gradually from the first end layer toward the second end layer.

3. (previously presented): The pn junction type Group III nitride semiconductor light-emitting device according to claim 1, wherein the second end layer has an impurity concentration low at its junction portion relative to the well layer, highest at its central portion and reduced gradually from the central portion toward the p-type clad layer.

4. (previously presented): The pn junction type Group III nitride semiconductor light-emitting device according to claim 1, wherein the second end layer has joined thereto a well layer which is not intentionally doped with impurities.